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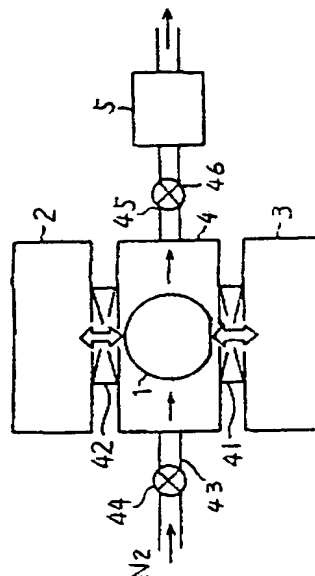
APPLICATION DATE : 19-01-89
APPLICATION NUMBER : 01012603

APPLICANT : FUJITSU LTD;

INVENTOR : UEDA YOSHITO;

INT.CL. : H01L 21/02

TITLE : MANUFACTURE OF
SEMICONDUCTOR DEVICE



ABSTRACT : PURPOSE: To prevent adhesion of dust to the wafers to be processed and to the processed wafers by a method wherein ionized gas is blown against the wafers, and the electric charge of the electrostatically adhered dust is neutralized.

CONSTITUTION: A first gate 41 is provided between a reserve vacuum chamber 4 and a wafer cassette part 3, and a second gate 42 is provided between the reserve vacuum chamber 4 and a vacuum chamber 2. Also, a gas-introducing piping 43 is connected to one side face of the reserve vacuum chamber 4 through the intermediary of an ionizing device 6, and a gas exhausting piping 45 is connected to other side face of the reserve vacuum chamber 4. A first cock 44 is provided in the midway of the gas-introducing piping 43, a second cock 46 is provided midway on the gas-exhausting piping 45, and a vacuum pump 5 is connected thereto. In this case, ionized gas is blown against a wafer 1 which passes through the reserve vacuum chamber 45, the electric charge of dust is neutralized electrostatically. As a result, the generation of a throw vent can be prevented, and the quantity of dust adhered to the wafer can also be reduced.

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